

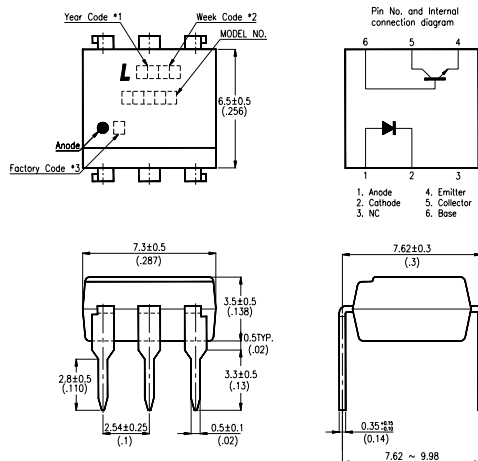
### Features

- High input-output isolation voltage  
(  $V_{ISO} = 5,000V_{rms}$  )
- Current transfer ratio  
( CTR : MIN. 10% at  $I_F = 10mA$ ,  $V_{CE} = 10V$  )
- UL approved ( No. E113898 )
- VDE approved ( No. 094722 )
- FIMKO approved ( No.209049 )
- SEMKO approved ( No. 9943380/01-20 )
- NEMKO approved ( No. P99102464 )
- DEMKO approved ( No. 99-04182 )
- CSA approve in progress
- Options Available :
  - Leads with 0.4" (10.16mm) Spacing (M Type)
  - Lead Bends for Surface Mounting (S Type)
  - Tape and Reel of Type I for SMD (Add "-TA" Suffix)
  - Tape and Reel of Type II for SMD (Add "-TA1" Suffix)
  - VDE 0884 Approvals (Add "-V" Suffix)

### Applications

1. General Purpose Switching Circuits
2. Interfacing and coupling systems of different potentials and impedances
3. Monitor and detection circuits

### Package Dimensions



### NOTES :

1. Year date code.
2. 2-digit work week.
3. Factory code shall be marked (Z : Taiwan, Y : Thailand).
4. Model No.: H11A1 ; H11A2 ; H11A3 ; H11A4 ; H11A5
5. All dimensions are in millimeters (inches).
6. Tolerance is  $\pm 0.25mm$  (.010") unless otherwise noted.
7. Specifications are subject to change without notice.

## Ordering Information

Part Number	Package	Safety Standard Approval	Application part number
H11A1 H11A1M H11A1S H11A1S-TA H11A1S-TA1	6-pin DIP 6-pin (leads with 0.4" spacing) 6-pin (lead bends for surface mount) 6-pin (tape and reel packaging of type I) 6-pin (tape and reel packaging of type II)	<ul style="list-style-type: none"> <li>• UL approved</li> <li>• FIMKO approved</li> <li>• SEMKO approved</li> <li>• DEMKO approved</li> <li>• NEMKO approved</li> <li>• CSA approve in progress</li> </ul>	H11A1
H11A2 H11A2M H11A2S H11A2S-TA H11A2S-TA1	6-pin DIP 6-pin (leads with 0.4" spacing) 6-pin (lead bends for surface mount) 6-pin (tape and reel packaging of type I) 6-pin (tape and reel packaging of type II)		H11A2
H11A3 H11A3M H11A3S H11A3S-TA H11A3S-TA1	6-pin DIP 6-pin (leads with 0.4" spacing) 6-pin (lead bends for surface mount) 6-pin (tape and reel packaging of type I) 6-pin (tape and reel packaging of type II)		H11A3
H11A4 H11A4M H11A4S H11A4S-TA H11A4S-TA1	6-pin DIP 6-pin (leads with 0.4" spacing) 6-pin (lead bends for surface mount) 6-pin (tape and reel packaging of type I) 6-pin (tape and reel packaging of type II)		H11A4
H11A5 H11A5M H11A5S H11A5S-TA H11A5S-TA1	6-pin DIP 6-pin (leads with 0.4" spacing) 6-pin (lead bends for surface mount) 6-pin (tape and reel packaging of type I) 6-pin (tape and reel packaging of type II)		H11A5
H11A1-V H11A1M-V H11A1S-V H11A1STA-V H11A1STA1-V	6-pin DIP 6-pin (leads with 0.4" spacing) 6-pin (lead bends for surface mount) 6-pin (tape and reel packaging of type I) 6-pin (tape and reel packaging of type II)	<ul style="list-style-type: none"> <li>• VDE approved</li> </ul>	H11A1
H11A2-V H11A2M-V H11A2S-V H11A2STA-V H11A2STA1-V	6-pin DIP 6-pin (leads with 0.4" spacing) 6-pin (lead bends for surface mount) 6-pin (tape and reel packaging of type I) 6-pin (tape and reel packaging of type II)		H11A2
H11A3-V H11A3M-V H11A3S-V H11A3STA-V H11A3STA1-V	6-pin DIP 6-pin (leads with 0.4" spacing) 6-pin (lead bends for surface mount) 6-pin (tape and reel packaging of type I) 6-pin (tape and reel packaging of type II)		H11A3
H11A4-V H11A4M-V H11A4S-V H11A4STA-V H11A4STA1-V	6-pin DIP 6-pin (leads with 0.4" spacing) 6-pin (lead bends for surface mount) 6-pin (tape and reel packaging of type I) 6-pin (tape and reel packaging of type II)		H11A4
H11A5-V H11A5M-V H11A5S-V H11A5STA-V H11A5STA1-V	6-pin DIP 6-pin (leads with 0.4" spacing) 6-pin (lead bends for surface mount) 6-pin (tape and reel packaging of type I) 6-pin (tape and reel packaging of type II)		H11A5

## Ratings and Characteristics

### Absolute Maximum Ratings

(Ta=25°C)

Parameter		Symbol	Rating	Unit
Input	Forward Current	I <sub>F</sub>	60	mA
	Reverse Voltage	V <sub>R</sub>	6	V
	Power Dissipation	P	100	mW
Output	Collector-Emitter Voltage	V <sub>CEO</sub>	30	V
	Emitter-Collector Voltage	V <sub>ECO</sub>	7	V
	Collector-Base Voltage	V <sub>CBO</sub>	70	V
	Collector Current	I <sub>C</sub>	150	mA
	Collector Power Dissipation	P <sub>C</sub>	150	mW
Total Power Dissipation		P <sub>tot</sub>	250	mW
*1.Isolation Voltage		V <sub>iso</sub>	5,000	V <sub>rms</sub>
Operating Temperature		T <sub>opr</sub>	-55~+100	°C
Storage Temperature		T <sub>stg</sub>	-55~+150	°C
*2.Soldering Temperature		T <sub>sol</sub>	260	°C

\*1. AC for 1 minute, R.H. = 40 ~ 60%

Isolation voltage shall be measured using the following method.

- (1) Short between anode and cathode on the primary side and between collector and emitter on the secondary side.
- (2) The isolation voltage tester with zero-cross circuit shall be used.
- (3) The waveform of applied voltage shall be a sine wave.

\*2. For 10 seconds

### Absolute Maximum Ratings

(Ta=25°C)

Parameter			Symbol	Min.	Typ.	Max.	unit	Conditions
Input	Forward Voltage		V <sub>F</sub>	—	1.2	1.5	V	I <sub>F</sub> =10mA
	Reverse Current		I <sub>R</sub>	—	—	10	μA	V <sub>R</sub> =6V
	Terminal Capacitance		C <sub>t</sub>	—	18	—	pF	V=0, f=1MHz
Output	Collector Dark Current		I <sub>CEO</sub>	—	—	50	nA	V <sub>CE</sub> =10V, I <sub>F</sub> =0
	Collector-Emitter Breakdown Voltage		BV <sub>CER</sub>	30	—	—	V	I <sub>C</sub> =0.1mA, I <sub>F</sub> =0
	Emitter-Collector Breakdown Voltage		BV <sub>ECO</sub>	7	—	—	V	I <sub>E</sub> =10 μA, I <sub>F</sub> =0mA
	Collector-Base Breakdown Voltage		BV <sub>ECO</sub>	70	—	—	V	I <sub>C</sub> =0.1mA, I <sub>F</sub> =0
	Collector-Emitter Capacitance		C <sub>CE</sub>	—	12	—	pF	V=0V, f=1MHz
	Collector-Base Capacitance		C <sub>CB</sub>	—	17	—	pF	V <sub>CB</sub> =0V, f=1MHz
	Emitter-Base Capacitance		C <sub>EB</sub>	—	25	—	pF	V <sub>EB</sub> =0V, f=1MHz
Transfer Characteristics	*1 Current Transfer Ratio	H11A1	CTR	50	—	—	%	I <sub>F</sub> =10mA V <sub>CE</sub> =10V
		H11A2		20	—	—		
		H11A3		20	—	—		
		H11A4		10	—	—		
		H11A5		30	—	—		
	Collector-emitter Saturation Voltage		V <sub>CE(sat)</sub>	—	0.15	0.4	V	I <sub>F</sub> =10mA, I <sub>C</sub> =0.5mA
	Isolation Resistance		R <sub>iso</sub>	100	—	—	G Ω	DC500V 40~60% R.H.
	Floating Capacitance		C <sub>f</sub>	—	0.3	—	pF	V=0, f=1MHz
	Response Time (Rise)		t <sub>r</sub>	—	2.8	—	μs	V <sub>CC</sub> =10V, I <sub>C</sub> =10mA
	Response Time (Fall)		t <sub>f</sub>	—	4.5	—	μs	R <sub>L</sub> =100 Ω

\*1. CTR=  $\frac{I_C}{I_F} \times 100\%$

Typical Electrical/Optical Characteristic Curves  
(25°C Ambient Temperature Unless Otherwise Noted)

Fig.1 Forward Current vs.  
Ambient Temperature

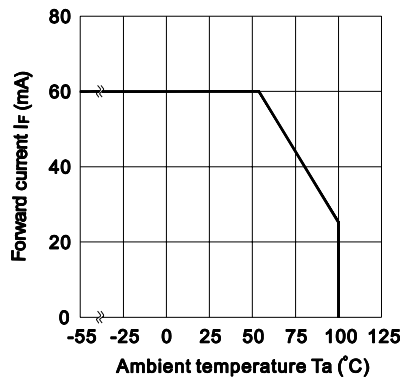


Fig.2 Collector Power Dissipation vs.  
Ambient Temperature

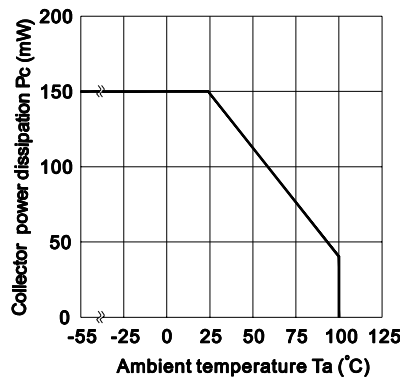


Fig.3 Collector-emitter saturation  
Voltage vs. Forward current

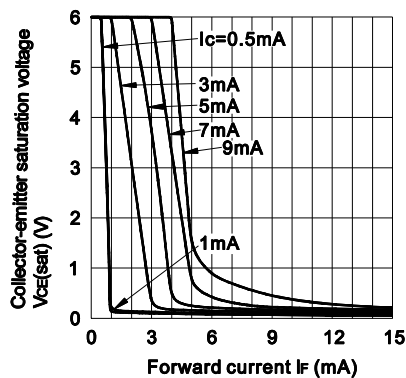


Fig.4 Turn-On Switching Times

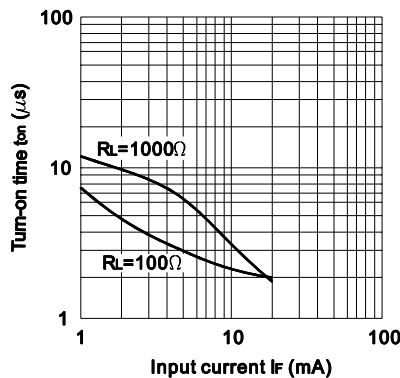


Fig.5 Current Transfer Ratio vs.  
Forward Current

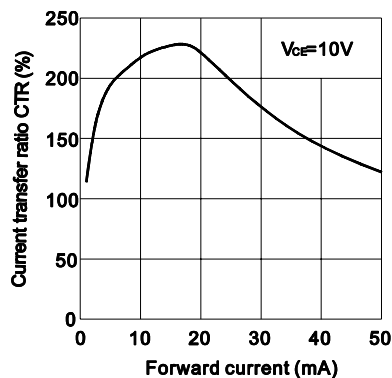


Fig.6 Collector Current vs.  
Collector-emitter Voltage

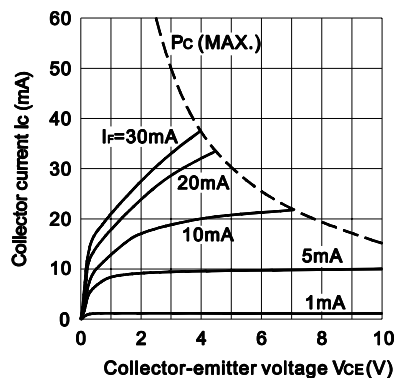


Fig.7 Rise and Fall Times

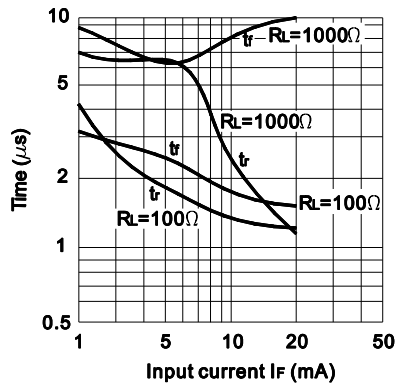
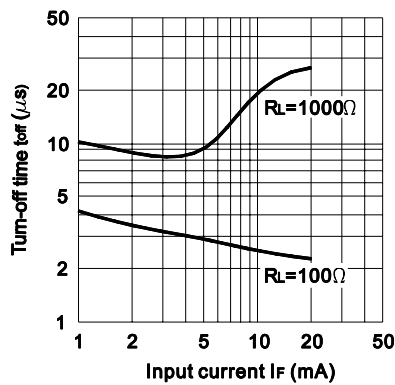
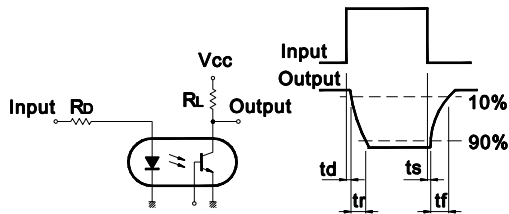


Fig.8 Turn-off Switching Times



Test Circuit for Response Time



Test Circuit for Frequency Response

